# 50C02CH

# Bipolar Transistor 50V, 0.5A, Low VCE(sat), NPN Single



# **ON Semiconductor®**

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• Large Current Capacitance

- Low Collector to Emitter Saturation Voltage (Resistance): RCE(sat) typ=175mΩ [IC=0.5A, IB=50mA]
- Ultrasmall Package Facilitates Miniaturization in End Products
- Small ON-Resistance (Ron)

## **Typical Applications**

- Low-Frequency Amplifier
- High Speed Switching
- Small Motor Drive
- Muting Circuit

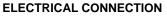
### SPECIFICATIONS

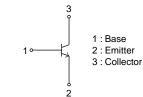
ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCEO	50	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	500	mA
Collector Current (Pulse)	ICP	1.0	А
Collector Dissipation (Note 2)	PC	700	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

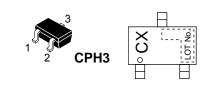
Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2 : Surface mounted on ceramic substrate( $600 \text{mm}^2 \times 0.8 \text{mm}$ )





### MARKING



### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

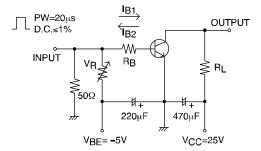
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## **ELECTRICAL CHARACTERISTICS** at $Ta = 25^{\circ}C$ (Note 3)

Devenueter	Parameter Symbol Conditions		Value			11
Parameter		min	typ	max	Unit	
Collector Cutoff Current	ICBO	V <sub>CB</sub> =40V, I <sub>E</sub> =0A			100	nA
Emitter Cutoff Current	IEBO	VEB=4V, IC=0A			100	nA
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =10mA 300			800	
Gain-Bandwidth Product	fT	VCE=10V, IC=50mA		500		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		2.8		pF
Collector to Emitter Saturation Voltage	V <sub>CE</sub> (sat)	IC=100mA, IB=10mA		50	100	mV
Base to Emitter Saturation Voltage	V <sub>BE</sub> (sat)	IC=100mA, IB=10mA		0.9	1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μΑ, I <sub>E</sub> =0Α	60			V
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter to Base Breakdown Voltage	V(BR)EBO	IE=10μΑ, IC=0Α	5			V
Turn-On Time	ton			30		ns
Storage Time	tstg	See specified Test		340		ns
Fall Time	tf			55		ns

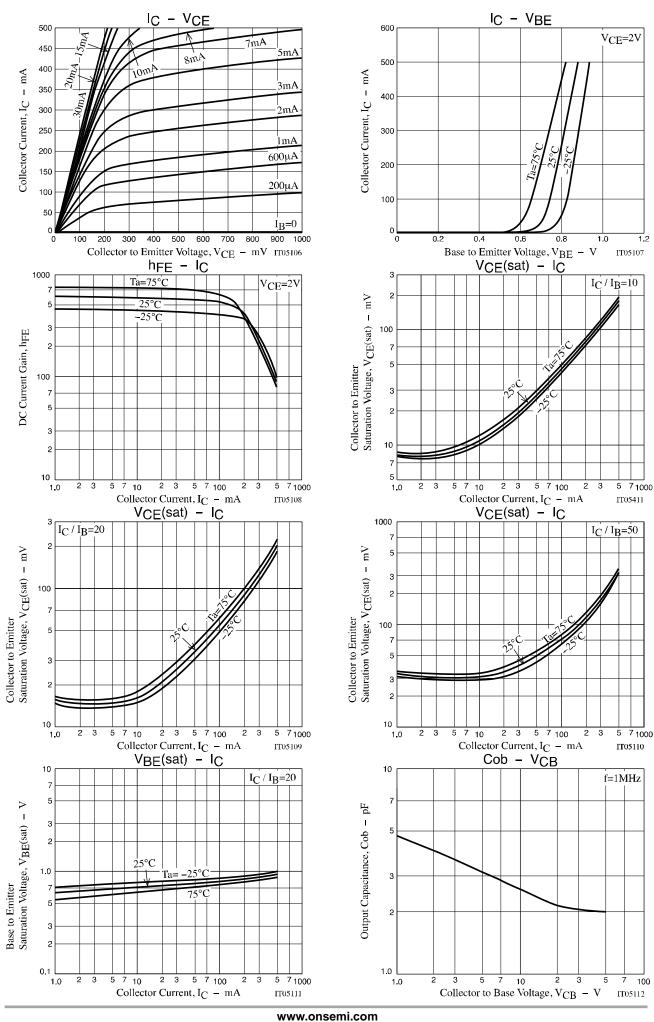
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## Switching Time Test Circuit

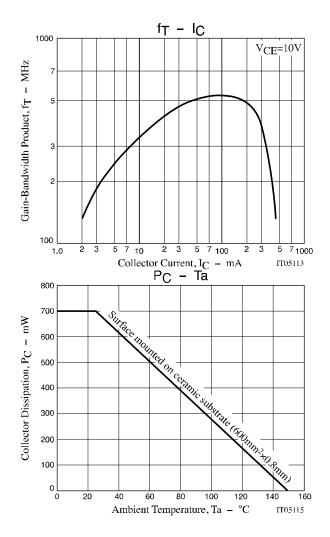


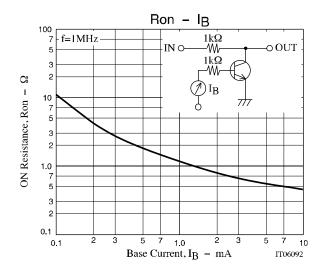
IC=20IB1= -20IB2=200mA

### 50C02CH



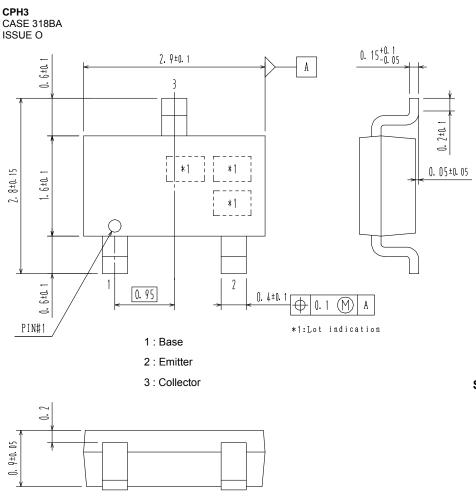
3



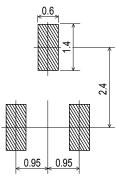


#### PACKAGE DIMENSIONS

unit : mm



Recommended Soldering Footprint



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)
50C02CH-TL-E	сх	CPH3 (Pb-Free)	3,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

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